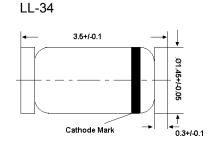
## **Silicon Schottky Barrier Diodes**

for general purpose applications



Glass case MiniMELF Dimensions in mm

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RRM</sub>	40	V
Continuous Forward Current	l <sub>F</sub>	30	mA
Repetitive Peak Forward Current $t_p \leq 1 \mbox{ s},  \delta \leq  0.5$	I <sub>FRM</sub>	150	mA
Repetitive Peak Forward Current t <sub>p</sub> = 1 s	I <sub>FSM</sub>	500	mA
Thermal Resistance from Junction to Ambient	R <sub>0JA</sub>	320	K/W
Junction Temperature	Tj	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to + 150	°C

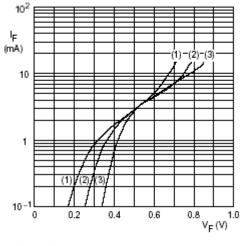
## Absolute Maximum Ratings ( $T_a = 25 \,^{\circ}C$ )

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1 \text{ mA}$ at $I_F = 1 \text{ mA}$ at $I_F = 15 \text{ mA}$	V <sub>F</sub>	0.33 0.41 1	V
Reverse Current at $V_R = 40$	I <sub>R</sub>	200	nA
Total Capacitance at $V_R$ = 2 V, f = 1 MHz	C <sub>tot</sub>	1.6	pF





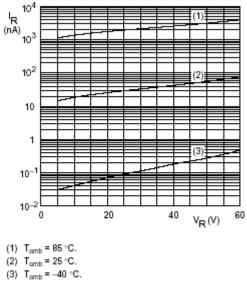




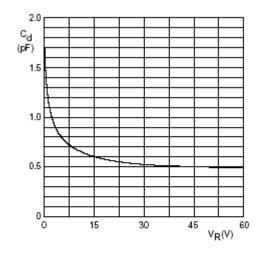
(1) T<sub>amb</sub> = 85 °C. (2) T<sub>amb</sub> = 25 °C.

(3) T<sub>amb</sub> = -40 °C.

Forward current as a function of forward voltage; typical values.



Reverse current as a function of reverse voltage; typical values.



f = 1 MHz.

Diode capacitance as a function of reverse voltage; typical values.



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